

*A⁺
cont.*

2. (Amended) The transistor of claim 1, wherein said layer of aluminum oxide is disposed upon said channel region, said aluminum nitride disposed over said aluminum oxide.

3. (Amended) The transistor of claim 1, wherein said layer of aluminum oxide is disposed over said channel region, said aluminum nitride disposed under said aluminum oxide.

*B1
cont'd.*

4. (Amended) The transistor of claim 1, wherein said layer of silicon dioxide is disposed upon said channel region, said aluminum nitride disposed over said silicon dioxide.

5. (Amended) The transistor of claim 1, wherein said layer of silicon dioxide is disposed over said channel region, said aluminum nitride disposed under said silicon dioxide.

6. (Amended) The transistor of claim 1, wherein said layer of silicon nitride is disposed upon said channel region, said aluminum nitride disposed over said silicon nitride.

7. (Amended) The transistor of claim 1, wherein said layer of silicon nitride is disposed over said channel region, said aluminum nitride disposed under said silicon nitride.

A2

11. (Amended) The transistor of claim 1, wherein said layer of aluminum oxide is disposed over said aluminum nitride.

15. (Amended) A semiconductor device, comprising:

a substrate comprising a source region, a drain region, and a channel region therebetween;

an insulating layer disposed over said channel region, said insulating layer comprising a

layer comprising aluminum nitride and at least one of aluminum oxide, silicon dioxide, and

silicon nitride disposed over said channel region; and

a gate electrode disposed over said insulating layer.

17. (Amended) A multi-terminal device, comprising:

a substrate comprising a source region, a drain region, and a channel region therebetween;

an insulating layer disposed over said channel region, said insulating layer comprising a

layer comprising aluminum nitride and at least one of aluminum oxide, silicon dioxide, and

silicon nitride disposed over said channel region; and

a gate electrode disposed over said insulating layer.